

	Type	Hits	Search Text	DBs
1	BRS	283660	si?n? or "si.sub.3 or n.sub.4" or nitride	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
2	BRS	48228	tft or thin adj film adj transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
3	BRS	1894	indium near2 zinc near2 oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
4	BRS	266	(indium near2 zinc near2 oxide) and (@ay = "2002")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
5	BRS	2039	(indium near2 zinc near2 oxide) or IZO	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
6	BRS	3771934	al or aluminum	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
7	BRS	17699	(al or aluminum) near8 gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
8	BRS	42	((tft or thin adj film adj transistor) and (si?n? or "si.sub.3 or n.sub.4" or nitride) same ((al or aluminum) near8 gate) and (indium near2 zinc near2 oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
9	BRS	9	((tft or thin adj film adj transistor) and (si?n? or "si.sub.3 or n.sub.4" or nitride) same ((al or aluminum) near8 gate) and (indium near2 zinc near2 oxide)) and (@ay < "2000")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

	Type	Hits	Search Text	DBs
10	BRS	2	20010019129.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
11	BRS	0	20010019129.pn. and "4" near2 micron	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
12	BRS	0	20010019129.pn. and micron	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
13	BRS	0	20010019129.pn. and micrometer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
14	BRS	0	20010019129.pn. and mu	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
15	BRS	0	20010019129.pn. and ".mu."	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
16	BRS	0	20010019129.pn. and ".mum."	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
17	BRS	2061	(indium near2 zinc near2 oxide) or IZO or InZnO or IZnO	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
18	BRS	45	(tft or thin adj film adj transistor) and (si?n? or "si.sub.3 or n.sub.4" or nitride) same ((al or aluminum) near8 gate) and ((indium near2 zinc near2 oxide) or IZO or InZnO or IZnO)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

	Type	Hits	Search Text	DBs
19	BRS	9	((tft or thin adj film adj transistor) and (si?n? or "si.sub.3 or n.sub.4" or nitride) same ((al or aluminum) near8 gate) and ((indium near2 zinc near2 oxide) or IZO or InZnO or IZnO)) and (@ay < "2000")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
20	BRS	707	(tft or thin adj film adj transistor) and ((indium near2 zinc near2 oxide) or IZO or InZnO or IZnO)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
21	BRS	98	((tft or thin adj film adj transistor) and ((indium near2 zinc near2 oxide) or IZO or InZnO or IZnO)) and (@ay < "2000")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
22	BRS	48228	tft or thin adj film adj transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
23	BRS	707	(tft or thin adj film adj transistor) and ((indium near2 zinc near2 oxide) or IZO or InZnO or IZnO)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
24	BRS	98	((tft or thin adj film adj transistor) and ((indium near2 zinc near2 oxide) or IZO or InZnO or IZnO)) and (@ay < "2000")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
25	BRS	2	20010019129.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
26	BRS	2	20010019129.pn. and gate near2 pad	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
27	BRS	2	6072450.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

	Type	Hits	Search Text	DBs
28	BRS	0	6072450.pn. and gate near2 (hole or pad)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
29	BRS	1	6072450.pn. and gate near8 (hole or pad)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
30	BRS	1	6072450.pn. and gate near8 (hole or pad or contact)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
31	BRS	48228	tft or thin adj film adj transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
32	BRS	3771934	al or aluminum	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
33	BRS	158598	data near2 (line or wire)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
34	BRS	86994	gate near4 (line or wire)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
35	BRS	4930	gate near4 (line or wire or electrode) near4 (al or aluminum)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
36	BRS	629	(data near2 (line or wire)) near4 (al or aluminum)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

	Type	Hits	Search Text	DBs
37	BRS	39	(gate near4 (line or wire or electrode) near4 (al or aluminum)) and ((data near2 (line or wire)) near4 (al or aluminum)) and (tft or thin adj film adj transistor) and (@ay < "2000")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
38	BRS	48228	tft or thin adj film adj transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
39	BRS	39	(gate near4 (line or wire or electrode) near4 (al or aluminum)) and ((data near2 (line or wire)) near4 (al or aluminum)) and (tft or thin adj film adj transistor) and (@ay < "2000")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
40	IS&R	2643	((257/347) or (257/771) or (257/776)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB